

=> d his

(FILE 'HOME' ENTERED AT 14:04:57 ON 08 APR 2004)

FILE 'REGISTRY' ENTERED AT 14:05:08 ON 08 APR 2004

L1 STRUCTURE UPLOADED  
L2 QUE L1  
L3 50 S L2 SSS SAM

FILE 'HCAPLUS, CAPLUS, USPATFULL' ENTERED AT 14:06:02 ON 08 APR 2004

L4 274 S L3  
L5 5555 S PHOTOACID GENERATOR  
L6 6236 S ACID GENERATOR  
L7 10641 S L5 OR L6  
L8 177 S L7 AND L4  
L9 96 DUPLICATE REMOVE L8 (81 DUPLICATES REMOVED)  
L10 96 S L9 AND (RESIST OR PHOTORESIST)  
L11 1732863 S POSITIVE  
L12 71 S L11 AND L10  
L13 71 DUPLICATE REMOVE L12 (0 DUPLICATES REMOVED)  
L14 131211 S PERFLUORO? OR PERHALO?

=> s l13 not l14

L15 48 L13 NOT L14

=> d l15 1-48 ibib hitstr

L15 ANSWER 1 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN

ACCESSION NUMBER: 2004:178264 HCAPLUS

DOCUMENT NUMBER: 140:225799

TITLE: Positive resist compositions with excellent sensitivity to high-energy beams and reduced line-edge roughness

INVENTOR(S): Yasunami, Shoichiro; Takahashi, Omote; Mizutani, Kazuyoshi

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 35 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2004070147	A2	20040304	JP 2002-231477	20020808
US 2004043323	A1	20040304	US 2003-634954	20030806

PRIORITY APPLN. INFO.: JP 2002-231477 A 20020808

IT 666256-52-6

RL: CAT (Catalyst use); USES (Uses)

(acid generator; pos. resist

comps. with good sensitivity and reduced line-edge roughness containing acid-labile polymers bearing protected phenolic OH groups and/or protected carboxyl groups)

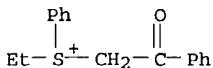
RN 666256-52-6 HCAPLUS

CN Sulfonium, ethyl(2-oxo-2-phenylethyl)phenyl-, salt with 1,1,2,2,3,3,4,4,4-nonafluoro-1-butan-1-sulfonic acid (1:1) (CA INDEX NAME)

CM 1

CRN 666256-51-5

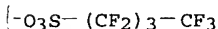
CMF C16 H17 O S



CM 2

CRN 45187-15-3

CMF C4 F9 O3 S



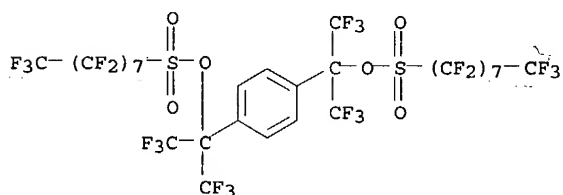
L15 ANSWER 2 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN

ACCESSION NUMBER: 2004:32911 HCAPLUS

DOCUMENT NUMBER: 140:102025  
 TITLE: Photoresists containing sulfonate ester photoacid generators providing patterns with good edge sharpness  
 INVENTOR(S): Kanna, Shinichi; Mizutani, Kazuyoshi; Sasaki, Tomoya  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 39 pp.  
 CODEN: JKXXAF  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2004012874	A2	20040115	JP 2002-167145	20020607

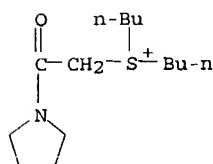
PRIORITY APPLN. INFO.: JP 2002-167145 20020607  
 OTHER SOURCE(S): MARPAT 140:102025  
 IT 643024-49-1  
 RL: CAT (Catalyst use); TEM (Technical or engineered material use); USES (Uses)  
 (photoacid generators; photoresists containing sulfonate ester photoacid generators)  
 RN 643024-49-1 HCAPLUS  
 CN 1-Octanesulfonic acid, 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-, 1,4-phenylenebis[2,2,2-trifluoro-1-(trifluoromethyl)ethylidene] ester (9CI) (CA INDEX NAME)



L15 ANSWER 3 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
 ACCESSION NUMBER: 2003:853314 HCAPLUS  
 DOCUMENT NUMBER: 139:343479  
 TITLE: Sulfonium compounds as radiation-sensitive acid generators and resist compositions containing them  
 INVENTOR(S): Kodama, Kunihiro  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 66 pp.  
 CODEN: JKXXAF  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003307839	A2	20031031	JP 2002-112372	20020415

PRIORITY APPLN. INFO.: JP 2002-112372 20020415  
 OTHER SOURCE(S): MARPAT 139:343479  
 IT 617692-33-8 617692-47-4  
 RL: CAT (Catalyst use); USES (Uses)  
 (preparation of sulfonium compds. having amide or sulfonamide linkage as radiation-sensitive acid generators and resist compns. containing them)  
 RN 617692-33-8 HCAPLUS  
 CN Sulfonium, dibutyl[2-oxo-2-(1-pyrrolidinyl)ethyl]-, salt with 1,1,2,2,3,3,4,4,4-nonafluoro-1-butanefluorobutanesulfonic acid (1:1) (9CI) (CA INDEX NAME)  
 CM 1  
 CRN 617692-32-7  
 CMF C14 H28 N O S



CM 2

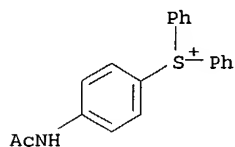
CRN 45187-15-3  
CMF C4 F9 O3 S

$^{-}O_3S^{-}(CF_2)_3-CF_3$ ,

RN 617692-47-4 HCAPLUS  
CN Sulfonium, [4-(acetylamino)phenyl]diphenyl-, salt with  
1,1,2,2,3,3,4,4,4-nonafluoro-1-butanesulfonic acid (1:1) (9CI) (CA INDEX  
NAME)

CM 1

CRN 112406-09-4  
CMF C20 H18 N O S



CM 2

CRN 45187-15-3  
CMF C4 F9 O3 S

$^{-}O_3S^{-}(CF_2)_3-CF_3$

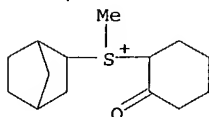
L15 ANSWER 4 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2003:470377 HCAPLUS  
DOCUMENT NUMBER: 139:44224  
TITLE: Positive-working resist  
composition containing specific fluorine  
group-containing resin  
INVENTOR(S): Kanna, Shinichi; Mizutani, Kazuyoshi; Kodama,  
Kunihiko; Sasaki, Tomoya  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Eur. Pat. Appl., 80 pp.  
CODEN: EPXXDW  
DOCUMENT TYPE: Patent  
LANGUAGE: English  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1319981	A2	20030618	EP 2002-27667	20021212
EP 1319981	A3	20030723		
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, SK				
US 2003194650	A1	20031016	US 2002-317110	20021212
JP 2003241386	A2	20030827	JP 2002-362629	20021213
PRIORITY APPLN. INFO.:			JP 2001-380104	A 20011213
			JP 2001-380105	A 20011213

IT 454471-17-1 454471-22-8 454471-25-1  
RL: TEM (Technical or engineered material use); USES (Uses)  
(photoacid generators)  
RN 454471-17-1 HCAPLUS  
CN Sulfonium, bicyclo[2.2.1]hept-2-ylmethyl(2-oxocyclohexyl)-, salt with  
1,1,2,2,3,3,4,4,4-nonafluoro-1-butanesulfonic acid (1:1) (9CI) (CA INDEX  
NAME)

CM 1

CRN 171292-11-8  
CMF C14 H23 O S



CM 2

CRN 45187-15-3  
CMF C4 F9 O3 S

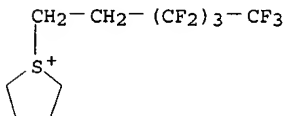
$^{-}\text{O}_3\text{S}-(\text{CF}_2)_3-\text{CF}_3$

RN 454471-22-8 HCAPLUS

CN Thiophenium, tetrahydro-1-(3,3,4,4,5,5,6,6,6-nonafluorohexyl)-, salt with 1,1,2,2,3,3,4,4,4-nonafluoro-1-butanesulfonic acid (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 454471-21-7  
CMF C10 H12 F9 S



CM 2

CRN 45187-15-3  
CMF C4 F9 O3 S

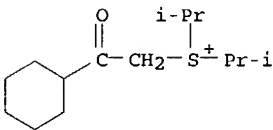
$^{-}\text{O}_3\text{S}-(\text{CF}_2)_3-\text{CF}_3$

RN 454471-25-1 HCAPLUS

CN Sulfonium, (2-cyclohexyl-2-oxoethyl)bis(1-methylethyl)-, salt with 1,1,2,2,3,3,4,4,4-nonafluoro-1-butanesulfonic acid (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 454471-24-0  
CMF C14 H27 O S



CM 2

CRN 45187-15-3  
CMF C4 F9 O3 S

$^{-}\text{O}_3\text{S}-(\text{CF}_2)_3-\text{CF}_3$

L15 ANSWER 5 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN

ACCESSION NUMBER: 2003:371832 HCAPLUS

DOCUMENT NUMBER: 138:376420

TITLE: Chemically amplified **positive** photoresists for micropatterns with minimized edge roughness

INVENTOR(S): Kodama, Kunihiro

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 60 pp.

CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003140344	A2	20030514	JP 2001-337884	20011102

PRIORITY APPLN. INFO.: JP 2001-337884 20011102

OTHER SOURCE(S): MARPAT 138:376420

IT 478837-88-6

RL: CAT (Catalyst use); TEM (Technical or engineered material use); USES (Uses)

(acid generators; amplified pos.

photoresists containing hydroxy-substituted sulfonium salts and forming patterns with minimized edge roughness)

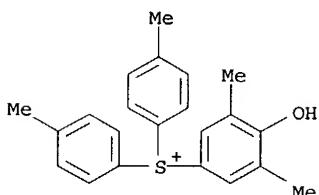
RN 478837-88-6 HCAPLUS

CN Sulfonium, (4-hydroxy-3,5-dimethylphenyl)bis(4-methylphenyl)-, salt with 1,1,2,2,3,3,4,4,4-nonafluoro-1-butanefluoro-1-butanesulfonic acid (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 478837-87-5

CMF C22 H23 O S



CM 2

CRN 45187-15-3

CMF C4 F9 O3 S

$^{-}O_3S^{-}(CF_2)_3-CF_3$

L15 ANSWER 6 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN

ACCESSION NUMBER: 2003:111387 HCAPLUS

DOCUMENT NUMBER: 138:178234

TITLE: Positive-working photoresist composition containing at least two acid-sensitive resins of acid-sensitive groups

INVENTOR(S): Sato, Kenichiro

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 51 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003043690	A2	20030213	JP 2001-236460	20010803

PRIORITY APPLN. INFO.: JP 2001-236460 20010803

IT 258341-99-0

RL: TEM (Technical or engineered material use); USES (Uses)

(acid-generator; pos.-working

photoresist composition)

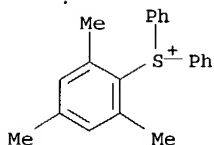
RN 258341-99-0 HCAPLUS

CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with 1,1,2,2,3,3,4,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6

CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

$^{-}\text{O}_3\text{S}- (\text{CF}_2)_7-\text{CF}_3$

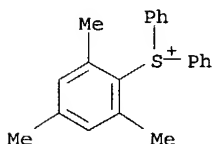
L15 ANSWER 7 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2003:17561 HCAPLUS  
DOCUMENT NUMBER: 138:98191  
TITLE: **Positive DUV resist compositions**  
having good SEM resistance, good resolution, and wide  
defocus latitude  
INVENTOR(S): Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 52 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003005374	A2	20030108	JP 2001-188414	20010621

PRIORITY APPLN. INFO.: JP 2001-188414 20010621  
IT 258341-99-0  
RL: CAT (Catalyst use); USES (Uses)  
(photoacid generator; pos. DUV  
resist compns. containing blend lactone polymers having good SEM  
resistance, good resolution, and wide defocus latitude)  
RN 258341-99-0 HCAPLUS  
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

$^{-}\text{O}_3\text{S}- (\text{CF}_2)_7-\text{CF}_3$

L15 ANSWER 8 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2002:963783 HCAPLUS  
DOCUMENT NUMBER: 138:47312  
TITLE: **Positive resist composition**  
INVENTOR(S): Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Eur. Pat. Appl., 69 pp.  
CODEN: EPXXDW  
DOCUMENT TYPE: Patent  
LANGUAGE: English  
FAMILY ACC. NUM. COUNT: 1

## PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1267210	A2	20021218	EP 2002-12454	20020611
EP 1267210	A3	20031008		
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR				
US 2003077543	A1	20030424	US 2002-165976	20020611
JP 2003177538	A2	20030627	JP 2002-170065	20020611
PRIORITY APPLN. INFO.:			JP 2001-177158	A 20010612
			JP 2001-308717	A 20011004

IT 258341-99-0 478837-88-6

RL: TEM (Technical or engineered material use); USES (Uses)  
 (photoacid generator; pos.  
 photoresist composition containing)

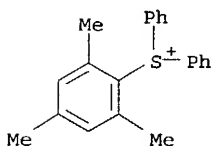
RN 258341-99-0 HCAPLUS

CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
 (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6

CMF C21 H21 S



CM 2

CRN 45298-90-6

CMF C8 F17 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

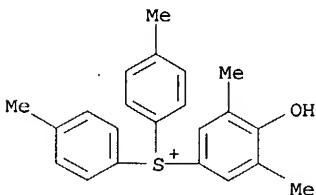
RN 478837-88-6 HCAPLUS

CN Sulfonium, (4-hydroxy-3,5-dimethylphenyl)bis(4-methylphenyl)-, salt with  
 1,1,2,2,3,3,4,4,4-nonafluoro-1-butan-1-yl sulfonic acid (1:1) (9CI) (CA INDEX  
 NAME)

CM 1

CRN 478837-87-5

CMF C22 H23 O S



CM 2

CRN 45187-15-3

CMF C4 F9 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>3</sub>-CF<sub>3</sub>

L15 ANSWER 9 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN

ACCESSION NUMBER: 2002:904448 HCAPLUS

DOCUMENT NUMBER: 138:9656

TITLE: Positive photosensitive composition

INVENTOR(S): Kodama, Kunihiko; Sato, Kenichiro; Fujimori, Toru

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Eur. Pat. Appl., 145 pp.  
CODEN: EPXXDW  
DOCUMENT TYPE: Patent  
LANGUAGE: English  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

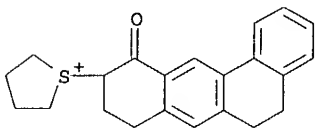
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1260864	A1	20021127	EP 2002-11516	20020522
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR				
JP 2002351077	A2	20021204	JP 2001-152587	20010522
JP 2002351079	A2	20021204	JP 2001-155897	20010524
JP 2002351063	A2	20021204	JP 2001-159060	20010528
US 2003077540	A1	20030424	US 2002-150967	20020521
PRIORITY APPLN. INFO.:			JP 2001-152587	A 20010522
			JP 2001-155897	A 20010524
			JP 2001-159060	A 20010528

OTHER SOURCE(S): MARPAT 138:9656

IT 477328-00-0P  
RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
(acid generator; pos photoresist composition containing)  
RN 477328-00-0 HCAPLUS  
CN Thiophenium, 1-(5,6,8,9,10,11-hexahydro-11-oxobenz[a]anthracen-10-yl)tetrahydro-, salt with 1,1,2,2,3,3,4,4,4-nonafluoro-1-butanefulfonic acid (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 477327-99-4  
CMF C22 H23 O S



CM 2

CRN 45187-15-3  
CMF C4 F9 O3 S

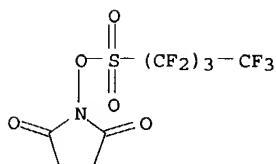
$^{-}O_3S-(CF_2)_3-CF_3$

REFERENCE COUNT: 9 THERE ARE 9 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

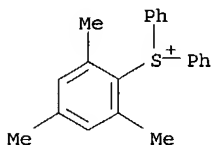
L15 ANSWER 10 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2002:901552 HCAPLUS  
DOCUMENT NUMBER: 137:391079  
TITLE: Positively-working photoresist composition containing polymer containing acrylate repeating unit with adamantyl group  
INVENTOR(S): Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 107 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002341540	A2	20021127	JP 2001-149861	20010518
PRIORITY APPLN. INFO.:			JP 2001-149861	20010518
IT 252937-66-9 258341-99-0				
RL: TEM (Technical or engineered material use); USES (Uses) (acid generator; pos.-working photoresist composition)				
RN 252937-66-9 HCAPLUS				
CN 2,5-Pyrrolidinedione, 1-[[[(nonafluorobutyl)sulfonyl]oxy]- (9CI) (CA INDEX NAME)				

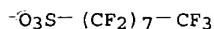




RN 258341-99-0 HCAPLUS  
 CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
 (1:1) (9CI) (CA INDEX NAME)  
 CM 1  
 CRN 47191-44-6  
 CMF C21 H21 S



CM 2  
 CRN 45298-90-6  
 CMF C8 F17 O3 S

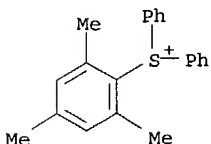


L15 ANSWER 11 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
 ACCESSION NUMBER: 2002:792710 HCAPLUS  
 DOCUMENT NUMBER: 137:317922  
 TITLE: Positive photoresist compositions  
 offering sharp patterns  
 INVENTOR(S): Sato, Kenichiro  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 85 pp.  
 CODEN: JKXXAF  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002303984	A2	20021018	JP 2001-135245	20010502
PRIORITY APPLN. INFO.:			JP 2001-22010	A 20010130
OTHER SOURCE(S):		MARPAT 137:317922		

IT 258341-99-0  
 RL: CAT (Catalyst use); USES (Uses)  
 (photoacid generator; pos.  
 photoresist compns. offering sharp patterns)  
 RN 258341-99-0 HCAPLUS  
 CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
 (1:1) (9CI) (CA INDEX NAME)

CM 1  
 CRN 47191-44-6  
 CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

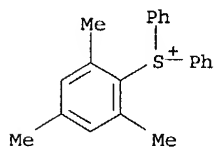
-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

L15 ANSWER 12 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2002:769998 HCAPLUS  
DOCUMENT NUMBER: 137:302221  
TITLE: Deep-UV **positive**-working photoresist  
composition showing improved contact hole resolution  
and sidelobe suppression  
INVENTOR(S): Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 77 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
	JP 2002296782	A2	20021009	JP 2001-101521	20010330
PRIORITY APPLN. INFO.:				JP 2001-101521	20010330
IT	258341-99-0				
RL:	CAT (Catalyst use); USES (Uses) (photoacid generator; deep-UV <b>pos</b> .-working photoresist composition showing improved contact hole resolution and side-lobe suppression)				
RN	258341-99-0	HCAPLUS			
CN	Sulfonium, diphenyl (2,4,6-trimethylphenyl)-, salt with 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid (1:1) (9CI) (CA INDEX NAME)				

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

L15 ANSWER 13 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN.  
ACCESSION NUMBER: 2002:688143 HCAPLUS  
DOCUMENT NUMBER: 137:239718  
TITLE: Photoacid generators in  
positive-working chemically amplified  
photoresist  
INVENTOR(S): Aogo, Toshiaki; Kodama, Kunihiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 65 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
	JP 2002255930	A2	20020911	JP 2001-57067	20010301
PRIORITY APPLN. INFO.:				JP 2001-57067	20010301
IT	459145-78-9P				
RL:	SPN (Synthetic preparation); TEM (Technical or engineered material)				

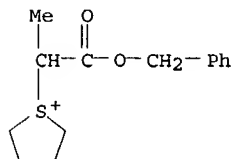
use); PREP (Preparation); USES (Uses)  
(photoacid generator in pos.-working  
chemical amplified photoresist)

RN 459145-78-9 HCAPLUS

CN Thiophenium, tetrahydro-1-[1-methyl-2-oxo-2-(phenylmethoxy)ethyl]-, salt  
with 1,1,2,2,3,3,4,4,4-nonafluoro-1-butanesulfonic acid (1:1) (9CI) (CA  
INDEX NAME)

CM 1

CRN 459145-77-8  
CMF C14 H19 O2 S



CM 2

CRN 45187-15-3  
CMF C4 F9 O3 S

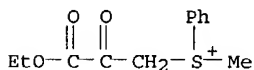
-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>3</sub>-CF<sub>3</sub>

RN 459145-94-9 HCAPLUS

CN Sulfonium, (3-ethoxy-2,3-dioxopropyl)methylphenyl-, salt with  
1,1,2,2,3,3,4,4,4-nonafluoro-1-butanesulfonic acid (1:1) (9CI) (CA INDEX  
NAME)

CM 1

CRN 459145-93-8  
CMF C12 H15 O3 S



CM 2

CRN 45187-15-3  
CMF C4 F9 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>3</sub>-CF<sub>3</sub>

L15 ANSWER 14 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN

ACCESSION NUMBER: 2002:673049 HCAPLUS

DOCUMENT NUMBER: 137:208381

TITLE: Storage-stable chemically amplified UV  
positive photoresist compositions  
with good post-exposure stability for halftone  
exposure

INVENTOR(S): Sato, Kenichiro; Kodama, Kunihiro

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 87 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 4

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002251013	A2	20020906	JP 2001-48880	20010223
US 2003017415	A1	20030123	US 2002-79414	20020222
PRIORITY APPLN. INFO.:			JP 2001-48602	A 20010223
			JP 2001-48783	A 20010223
			JP 2001-48784	A 20010223
			JP 2001-48880	A 20010223

JP 2001-157366 A 20010525  
JP 2001-157367 A 20010525

IT 454471-17-1 454471-22-8 454471-25-1

RL: CAT (Catalyst use); USES (Uses)  
(photoacid generator; storage-stable chemical  
amplified UV pos. photoresists with good  
post-exposure stability for halftone exposure)

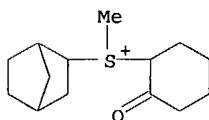
RN 454471-17-1 HCAPLUS

CN Sulfonium, bicyclo[2.2.1]hept-2-ylmethyl(2-oxocyclohexyl)-, salt with  
1,1,2,2,3,3,4,4,4-nonafluoro-1-butanesulfonic acid (1:1) (9CI) (CA INDEX  
NAME)

CM 1

CRN 171292-11-8

CMF C14 H23 O S



CM 2

CRN 45187-15-3

CMF C4 F9 O3 S

$^{-}O_3S^{-}(CF_2)_3-CF_3$

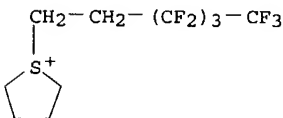
RN 454471-22-8 HCAPLUS

CN Thiophenium, tetrahydro-1-(3,3,4,4,5,5,6,6,6-nonafluorohexyl)-, salt with  
1,1,2,2,3,3,4,4,4-nonafluoro-1-butanesulfonic acid (1:1) (9CI) (CA INDEX  
NAME)

CM 1

CRN 454471-21-7

CMF C10 H12 F9 S



CM 2

CRN 45187-15-3

CMF C4 F9 O3 S

$^{-}O_3S^{-}(CF_2)_3-CF_3$

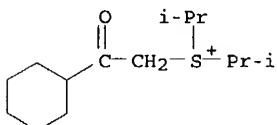
RN 454471-25-1 HCAPLUS

CN Sulfonium, (2-cyclohexyl-2-oxoethyl)bis(1-methylethyl)-, salt with  
1,1,2,2,3,3,4,4,4-nonafluoro-1-butanesulfonic acid (1:1) (9CI) (CA INDEX  
NAME)

CM 1

CRN 454471-24-0

CMF C14 H27 O S



CM 2

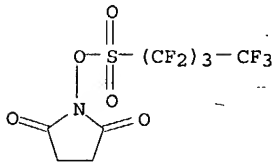
CRN 45187-15-3  
CMF C4 F9 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>3</sub>-CF<sub>3</sub>

L15 ANSWER 15 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2002:673045 HCAPLUS  
DOCUMENT NUMBER: 137:224107  
TITLE: Chemically amplified **positive-working far-UV photoresist** compositions suitable for halftone phase-shift masks  
INVENTOR(S): Sato, Kenichiro; Uenishi, Kazuya  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 104 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002251011	A2	20020906	JP 2001-48782	20010223

PRIORITY APPLN. INFO.: JP 2001-48782 20010223  
OTHER SOURCE(S): MARPAT 137:224107  
IT 252937-66-9  
RL: CAT (Catalyst use); USES (Uses)  
(photoacid generator; chemical amplified pos  
.-working far-UV photoresists suitable for halftone  
phase-shift masks)  
RN 252937-66-9 HCAPLUS  
CN 2,5-Pyrrolidinedione, 1-[[ (nonafluorobutyl)sulfonyl]oxy]- (9CI) (CA INDEX NAME)



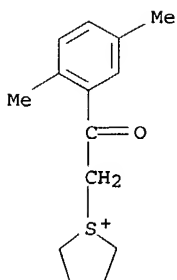
L15 ANSWER 16 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2002:636854 HCAPLUS  
DOCUMENT NUMBER: 137:177115  
TITLE: Chemically amplified **positive-working photoimaging** compositions for photofabrication by excimer lasers with high sensitivity and resolution  
INVENTOR(S): Kodama, Kunihiko  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 51 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002236359	A2	20020823	JP 2001-33923	20010209

PRIORITY APPLN. INFO.: JP 2001-33923 20010209  
OTHER SOURCE(S): MARPAT 137:177115  
IT 448959-49-7  
RL: CAT (Catalyst use); USES (Uses)  
(photoacid generator; chemical amplified pos  
.- photoresists for excimer lasers with high sensitivity and  
resolution)  
RN 448959-49-7 HCAPLUS  
CN Thiophenium, 1-[2-(2,5-dimethylphenyl)-2-oxoethyl]tetrahydro-, salt with 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 448194-88-5  
CMF C14 H19 O S



CM 2

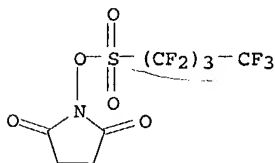
CRN 45298-90-6  
CMF C8 F17 03 S

$\text{O}_3\text{S}-(\text{CF}_2)_7-\text{CF}_3$

L15 ANSWER 17 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2002:566566 HCAPLUS  
DOCUMENT NUMBER: 137:132102  
TITLE: Positive-working photoresist composition  
INVENTOR(S): Fujimori, Toru  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 78 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002214786	A2	20020731	JP 2001-10481	20010118

PRIORITY APPLN. INFO.: JP 2001-10481 20010118  
IT 252937-66-9  
RL: TEM (Technical or engineered material use); USES (Uses)  
(acid generator in pos.-working photoresist composition)  
RN 252937-66-9 HCAPLUS  
CN 2,5-Pyrrolidinedione, 1-[[[nonafluorobutyl)sulfonyl]oxy]- (9CI) (CA INDEX NAME)



L15 ANSWER 18 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2002:539335 HCAPLUS  
DOCUMENT NUMBER: 137:101423  
TITLE: Storage-stable chemically amplified far-UV positive photoresist compositions suitable for half-tone phase-shift photomasks  
INVENTOR(S): Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 80 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

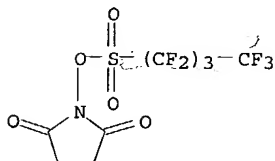
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002202605	A2	20020719	JP 2000-402244	20001228

PRIORITY APPLN. INFO.: JP 2000-402244 20001228  
OTHER SOURCE(S): MARPAT 137:101423  
IT 252937-66-9

RL: CAT (Catalyst use); USES (Uses)  
(photoacid generator; storage-stable far-UV  
pos. photoresists containing triphenylsulfonium  
photoacid generators for half-tone phase-shift  
photomasks)

RN 252937-66-9 HCAPLUS

CN 2,5-Pyrrolidinedione, 1-[[[nonafluorobutyl)sulfonyl]oxy]- (9CI) (CA INDEX  
NAME)



L15 ANSWER 19 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN

ACCESSION NUMBER: 2002:538441 HCAPLUS

DOCUMENT NUMBER: 137:116950

TITLE: Chemically amplified far-UV positive  
photoresists compositions with improved  
exposure margin and defocus latitude

INVENTOR(S): Sato, Kenichiro

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 81 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002202607	A2	20020719	JP 2000-402246	20001228

PRIORITY APPLN. INFO.: JP 2000-402246 20001228

OTHER SOURCE(S): MARPAT 137:116950

IT 421555-73-9

RL: CAT (Catalyst use); USES (Uses)

(photoacid generator; far-UV pos.

photoresists having sulfonium and iodonium photoacid

generators with improved exposure margin and defocus latitude)

RN 421555-73-9 HCAPLUS

CN Sulfonium, (thiodi-4,1-phenylene)bis[diphenyl-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,6-tridecafluoro-1-hexanesulfonic acid (1:2) (9CI)  
(CA INDEX NAME)

CM 1

CRN 108427-53-8

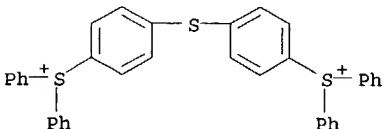
CMF C6 F13 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>5</sub>-CF<sub>3</sub>

CM 2

CRN 74227-34-2

CMF C36 H28 S3



L15 ANSWER 20 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN

ACCESSION NUMBER: 2002:464506 HCAPLUS

DOCUMENT NUMBER: 137:54616

TITLE: Positive-working photoresist  
composition for semiconductor device fabrication

INVENTOR(S): Sasaki, Tomoya; Mizutani, Kazuyoshi; Yasunami,  
Shoichiro

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 48 pp.

CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002174903	A2	20020621	JP 2000-373077	20001207
PRIORITY APPLN. INFO.:			JP 2000-373077	20001207

IT 258341-99-0

RL: TEM (Technical or engineered material use); USES (Uses)  
(acid generator in pos.-working  
photoresist composition for semiconductor device fabrication)

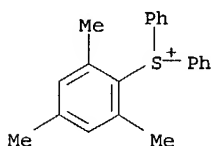
RN 258341-99-0 HCAPLUS

CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6

CMF C21 H21 S



CM 2

CRN 45298-90-6

CMF C8 F17 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

L15 ANSWER 21 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2002:347848 HCAPLUS  
DOCUMENT NUMBER: 136:361828  
TITLE: Positive-working photoresist  
compositions containing norbornene-acrylate copolymers  
INVENTOR(S): Sato, Kenichiro; Nakao, Hajime  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 80 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002131917	A2	20020509	JP 2001-169802	20010605
PRIORITY APPLN. INFO.:			JP 2000-174037	A 20000609
			JP 2000-186431	A 20000621
			JP 2000-206812	A 20000707
			JP 2000-206890	A 20000707
			JP 2000-211414	A 20000712
			JP 2000-215441	A 20000717
			JP 2000-248658	A 20000818

OTHER SOURCE(S): MARPAT 136:361828

IT 252937-66-9 258341-99-0 421555-73-9

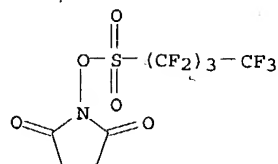
RL: CAT (Catalyst use); TEM (Technical or engineered material use); USES  
(Uses)

(photoacid generator; pos.-working  
photoresist compns. containing norbornene-acrylate copolymers)

RN 252937-66-9 HCAPLUS

CN 2,5-Pyrrolidinedione, 1-[[[(nonafluorobutyl)sulfonyl]oxy]- (9CI) (CA INDEX  
NAME)

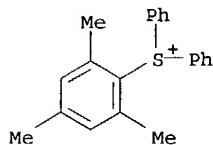




RN 258341-99-0 HCAPLUS  
 CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
 (1:1) (9CI) (CA INDEX NAME)

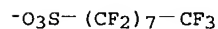
CM 1

CRN 47191-44-6  
 CMF C21 H21 S



CM 2

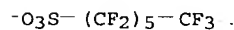
CRN 45298-90-6  
 CMF C8 F17 O3 S



RN 421555-73-9 HCAPLUS  
 CN Sulfonium, (thiodi-4,1-phenylene)bis[diphenyl]-, salt with  
 1,1,2,2,3,3,4,4,5,5,6,6,6-tridecafluoro-1-hexanesulfonic acid (1:2) (9CI)  
 (CA INDEX NAME)

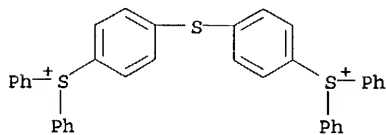
CM 1

CRN 108427-53-8  
 CMF C6 F13 O3 S



CM 2

CRN 74227-34-2  
 CMF C36 H28 S3

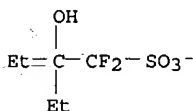


L15 ANSWER 22 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
 ACCESSION NUMBER: 2002:314503 HCAPLUS  
 DOCUMENT NUMBER: 136:348304  
 TITLE: Positive photosensitive composition  
 INVENTOR(S): Kodama, Kunihiro; Aoi, Toshiaki  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Eur. Pat. Appl., 148 pp.  
 CODEN: EPXXDW  
 DOCUMENT TYPE: Patent  
 LANGUAGE: English  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

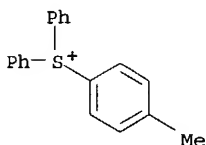
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1199603	A1	20020424	EP 2001-124329	20011019

R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT,  
 IE, SI, LT, LV, FI, RO, MK, CY, AL, TR  
 JP 2002131897 A2 20020509 JP 2000-321128 20001020  
 JP 2002214774 A2 20020731 JP 2001-132546 20010427  
 US 2002102491 A1 20020801 US 2001-978103 20011017  
 TW 536663 B 20030611 TW 2001-90125903 20011019  
 PRIORITY APPLN. INFO.: JP 2000-321128 A 20001020  
 JP 2000-352899 A 20001120  
 JP 2001-132546 A 20010427

IT 414911-73-2  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (photo-acid generator used in pos.  
 photoresist composition)  
 RN 414911-73-2 HCAPLUS  
 CN Sulfonium, (4-methylphenyl)diphenyl-, salt with 2-ethyl-1,1-difluoro-2-  
 hydroxy-1-butanefulfonic acid (1:1) (9CI) (CA INDEX NAME)  
 CM 1  
 CRN 414911-72-1  
 CMF C6 H11 F2 O4 S



CM 2  
 CRN 47045-31-8  
 CMF C19 H17 S

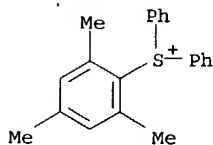


REFERENCE COUNT: 5 THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS  
 RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L15 ANSWER 23 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
 ACCESSION NUMBER: 2002:119603 HCAPLUS  
 DOCUMENT NUMBER: 136:191685  
 TITLE: Positively working photoresist composition  
 for far-ultraviolet exposure  
 INVENTOR(S): Nakao, Hajime; Sato, Kenichiro  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 55 pp.  
 CODEN: JKXXAF  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002049154	A2	20020215	JP 2000-233146	20000801

PRIORITY APPLN. INFO.: JP 2000-233146 20000801  
 OTHER SOURCE(S): MARPAT 136:191685  
 IT 258341-99-0  
 RL: CAT (Catalyst use); TEM (Technical or engineered material use); USES  
 (Uses)  
 (photoacid generator; pos.-working  
 photoresist composition for far-UV exposure)  
 RN 258341-99-0 HCAPLUS  
 CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
 (1:1) (9CI) (CA INDEX NAME)  
 CM 1  
 CRN 47191-44-6  
 CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

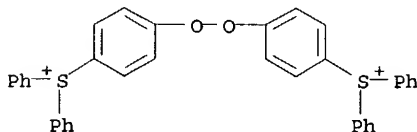
L15 ANSWER 24 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2002:65853 HCAPLUS  
DOCUMENT NUMBER: 136:126558  
TITLE: **Positive-working photoresist composition containing specific resin and photoacid generator**  
INVENTOR(S): Nakao, Hajime; Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 52 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002023376	A2	20020123	JP 2000-208514	20000710

PRIORITY APPLN. INFO.: JP 2000-208514 20000710  
OTHER SOURCE(S): MARPAT 136:126558  
IT 391232-45-4  
RL: TEM (Technical or engineered material use); USES (Uses)  
(photoacid generator in pos. working photoresist composition)  
RN 391232-45-4 HCAPLUS  
CN Sulfonium, (dioxidi-4,1-phenylene)bis(diphenyl-, salt with 1,1,2,2,3,3,4,4,4-nonafluoro-1-butanefulfonic acid (1:2) (9CI) (CA INDEX NAME)

CM 1

CRN 391232-44-3  
CMF C36 H28 O2 S2



CM 2

CRN 45187-15-3  
CMF C4 F9 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>3</sub>-CF<sub>3</sub>

L15 ANSWER 25 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2001:932743 HCAPLUS  
DOCUMENT NUMBER: 136:77249  
TITLE: **Positive-working two-layered photoresist**  
INVENTOR(S): Yasunami, Shoichiro; Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 51 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001356484	A2	20011226	JP 2000-178538	20000614
US 2002028409	A1	20020307	US 2001-880030	20010614
US 6696219	B2	20040224		

PRIORITY APPLN. INFO.: JP 2000-178538 A 20000614

IT 258341-99-0

RL: TEM (Technical or engineered material use); USES (Uses)  
(acid-generator in second resist layer of  
two-layered photoresist)

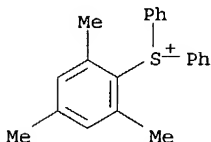
RN 258341-99-0 HCAPLUS

CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6

CMF C21 H21 S



CM 2

CRN 45298-90-6

CMF C8 F17 O3 S

$-\text{O}_3\text{S}-(\text{CF}_2)_7-\text{CF}_3$

L15 ANSWER 26 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2001:760378 HCAPLUS  
DOCUMENT NUMBER: 135:310932  
TITLE: Positive-working photoresist  
compositions for semiconductor device fabrication  
INVENTOR(S): Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 44 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001290273	A2	20011019	JP 2000-106810	20000407

PRIORITY APPLN. INFO.: JP 2000-106810 20000407

IT 258341-99-0P

RL: CAT (Catalyst use); PNU (Preparation, unclassified); PREP  
(Preparation); USES (Uses)  
(photoacid generator; pos.  
photoresist compns. with good post exposure delay stability  
containing resins having silyl group)

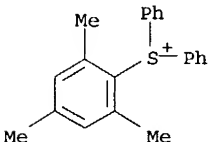
RN 258341-99-0 HCAPLUS

CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6

CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

$\text{O}_3\text{S}-(\text{CF}_2)_7-\text{CF}_3$

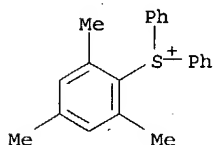
L15 ANSWER 27 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2001:726601 HCAPLUS  
DOCUMENT NUMBER: 135:280511  
TITLE: **Positive-working photoresist**  
compositions showing high resolution and high  
sensitivity and excellent storage stability  
INVENTOR(S): Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 62 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001272784	A2	20011005	JP 2000-385724	20001219
PRIORITY APPLN. INFO.:			JP 1999-363302	A 19991221
			JP 2000-10773	A 20000119
			JP 2000-10774	A 20000119

OTHER SOURCE(S): MARPAT 135:280511  
IT 258341-99-0P  
RL: PNU (Preparation, unclassified); TEM (Technical or engineered material  
use); PREP (Preparation); USES (Uses)  
(acid generator; alkaline-developing silyl-containing  
polymer pos. photoresists having storage stability)  
RN 258341-99-0 HCAPLUS  
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

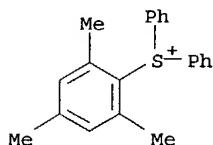
CRN 45298-90-6  
CMF C8 F17 O3 S

$\text{O}_3\text{S}-(\text{CF}_2)_7-\text{CF}_3$

L15 ANSWER 28 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2001:635654 HCAPLUS  
DOCUMENT NUMBER: 135:218725  
TITLE: **Positive-working far-UV photoresist**  
composition containing sulfonium salts as  
**photoacid generators**  
INVENTOR(S): Sato, Kenichiro; Mizutani, Kazuyoshi  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 35 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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JP 2001235869 A2 20010831 JP 2000-47971 20000224  
 PRIORITY APPLN. INFO.: JP 2000-47971 20000224  
 OTHER SOURCE(S): MARPAT 135:218725  
 IT 258341-99-0  
 RL: CAT (Catalyst use); USES (Uses)  
 (pos.-working far-UV photoresist composition containing  
 sulfonium salts as photoacid generators and  
 silylethoxycarbonyl-containing resins)  
 RN 258341-99-0 HCAPLUS  
 CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
 (1:1) (9CI) (CA INDEX NAME)  
 CM 1  
 CRN 47191-44-6  
 CMF C21 H21 S



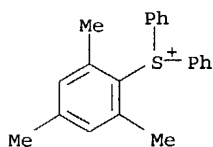
CM 2  
 CRN 45298-90-6  
 CMF C8 F17 O3 S

$-\text{O}_3\text{S}- (\text{CF}_2)_7-\text{CF}_3$

L15 ANSWER 29 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
 ACCESSION NUMBER: 2001:632163 HCAPLUS  
 DOCUMENT NUMBER: 135:203008  
 TITLE: Positive-working far-UV photoresist  
 compositions containing sulfonium or iodonium  
 fluoroalkanesulfonates  
 INVENTOR(S): Sato, Kenichiro; Mizutani, Kazuyoshi  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 36 pp.  
 CODEN: JKXXAF  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001235868	A2	20010831	JP 2000-47970	20000224

PRIORITY APPLN. INFO.: JP 2000-47970 20000224  
 OTHER SOURCE(S): MARPAT 135:203008  
 IT 258341-99-0 353264-92-3  
 RL: CAT (Catalyst use); USES (Uses)  
 (pos.-working far-UV photoresist compns. containing  
 sulfonium or iodonium fluoroalkanesulfonates as photoacid  
 generators and silylethoxycarbonyl-containing resins)  
 RN 258341-99-0 HCAPLUS  
 CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
 (1:1) (9CI) (CA INDEX NAME)  
 CM 1  
 CRN 47191-44-6  
 CMF C21 H21 S



CM 2

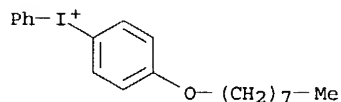
CRN 45298-90-6  
CMF C8 F17 O3 S

$^{-}\text{O}_3\text{S}-\text{(CF}_2\text{)}_7-\text{CF}_3$

RN 353264-92-3 HCAPLUS  
CN Iodonium, [4-(octyloxy)phenyl]phenyl-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptadecafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 121239-74-5  
CMF C20 H26 I O



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

$^{-}\text{O}_3\text{S}-\text{(CF}_2\text{)}_7-\text{CF}_3$

L15 ANSWER 30 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2001:579374 HCAPLUS  
DOCUMENT NUMBER: 135:160148  
TITLE: Positive-working chemically amplified  
photoresist composition  
INVENTOR(S): Sato, Kenichiro; Mizutani, Kazuyoshi  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 35 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

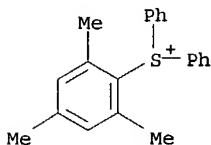
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001215706	A2	20010810	JP 2000-28104	20000204
PRIORITY APPLN. INFO.:			JP 2000-28104	20000204
OTHER SOURCE(S):		MARPAT 135:160148		

IT 258341-99-0 353264-92-3  
RL: TEM (Technical or engineered material use); USES (Uses)  
(photoacid generator in pos.-working  
chemical amplified photoresist composition)

RN 258341-99-0 HCAPLUS  
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptadecafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6

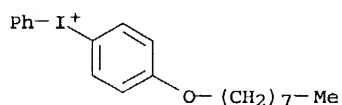
CMF C8 F17 O3 S

~~-O<sub>3</sub>S-~~ (CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

RN 353264-92-3 HCAPLUS  
CN Iodonium, [4-(octyloxy)phenyl]phenyl-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 121239-74-5  
CMF C20 H26 I O



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

~~-O<sub>3</sub>S-~~ (CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

L15 ANSWER 31 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2001:579373 HCAPLUS  
DOCUMENT NUMBER: 135:172985  
TITLE: Positive-working photoresist  
composition for manufacturing electric circuits such  
as contact hole pattern formation  
INVENTOR(S): Sato, Kenichiro; Mizutani, Kazuyoshi  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 35 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

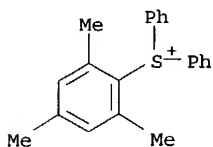
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001215705	A2	20010810	JP 2000-28103	20000204
PRIORITY APPLN. INFO.:			JP 2000-28103	20000204
OTHER SOURCE(S): MARPAT 135:172985				
IT 258341-99-0				

RL: TEM (Technical or engineered material use); USES (Uses)  
(photoacid-sensitive compound in pos.-working  
photoresist composition)

RN 258341-99-0 HCAPLUS  
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S



-O<sub>3</sub>S-(CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

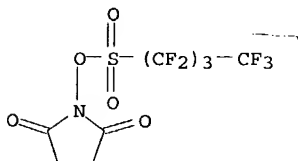
L15 ANSWER 32 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2001:534446 HCAPLUS  
DOCUMENT NUMBER: 135:129569  
TITLE: Chemically amplified **photoresist**  
compositions containing alkyl vinyl ether polymers for  
ArF excimer laser exposure  
INVENTOR(S): Choi, Sang Joon; Kim, Hyun Woo  
PATENT ASSIGNEE(S): Samsung Electronics Co., Ltd., S. Korea  
SOURCE: Jpn. Kokai Tokkyo Koho, 21 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 3  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001200016	A2	20010724	JP 2001-12171	20010119
EP 1120689	A2	20010801	EP 2001-300418	20010118
EP 1120689	A3	20010808		

R: AT, BE, CH, DE, DK, ES, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE,  
SI, LT, LV, FI, RO

PRIORITY APPLN. INFO.: KR 2000-2489 A 20000119  
KR 2000-20603 A 20000419

IT 252937-66-9  
RL: CAT (Catalyst use); USES (Uses)  
(photoacid generators; chemical amplified  
photoresists containing alkyl vinyl ether polymers for ArF excimer  
laser exposure)  
RN 252937-66-9 HCAPLUS  
CN 2,5-Pyrrolidinedione, 1-[[[nonafluorobutyl)sulfonyl]oxy]- (9CI) (CA INDEX  
NAME)



L15 ANSWER 33 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2001:523649 HCAPLUS  
DOCUMENT NUMBER: 135:114440  
TITLE: Positive-working chemically amplified  
photoresist composition  
INVENTOR(S): Sato, Kenichiro; Mizutani, Kazuyoshi  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 45 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001194788	A2	20010719	JP 2000-1895	20000107

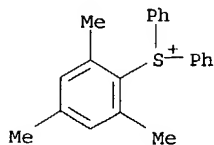
PRIORITY APPLN. INFO.: JP 2000-1895 20000107

IT 258341-99-0  
RL: TEM (Technical or engineered material use); USES (Uses)  
(photoacid generator in pos.-working  
chemical amplified photoresist)

RN 258341-99-0 HCAPLUS  
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

$-\text{O}_3\text{S}^-(\text{CF}_2)_7-\text{CF}_3$

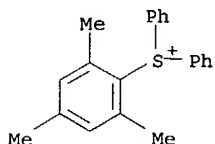
L15 ANSWER 34 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
 ACCESSION NUMBER: 2001:521143 HCAPLUS  
 DOCUMENT NUMBER: 135:114437  
 TITLE: **Positive-working photoresist**  
 composition for production of electric parts such as  
 semiconductor substrate with contact holes  
 INVENTOR(S): Sato, Kenichiro; Mizutani, Kazuyoshi  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 43 pp.  
 CODEN: JKXXAF  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001194789	A2	20010719	JP 2000-1896	20000107
PRIORITY APPLN. INFO.: JP 2000-1896			20000107	

IT 258341-99-0P  
 RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT  
 (Reactant or reagent)  
 (photoacid generator in pos.-working  
 photoresist composition)  
 RN 258341-99-0 HCAPLUS  
 CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
 (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

$-\text{O}_3\text{S}^-(\text{CF}_2)_7-\text{CF}_3$

L15 ANSWER 35 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
 ACCESSION NUMBER: 2001:423557 HCAPLUS  
 DOCUMENT NUMBER: 135:38893  
 TITLE: **Positive photoresist compositions**  
 for manufacture of semiconductor devices  
 INVENTOR(S): Sato, Kenichiro; Kodama, Kunihiro; Mizutani, Kazuyoshi  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 66 pp.  
 CODEN: JKXXAF  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 4  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001159812	A2	20010612	JP 1999-343714	19991202
US 6506535	B1	20030114	US 2000-698221	20001030

PRIORITY APPLN. INFO.: JP 1999-307317 A 19991028  
JP 1999-331785 A 19991122  
JP 1999-338487 A 19991129  
JP 1999-343714 A 19991202

OTHER SOURCE(S): MARPAT 135:38893

IT 258341-99-0

RL: TEM (Technical or engineered material use); USES (Uses)  
(photoacid generators; improvement of exposure  
margin in pos. photoresists for manufacture of  
semiconductor devices)

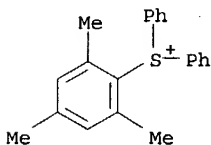
RN 258341-99-0 HCAPLUS

CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6

CMF C21 H21 S



CM 2

CRN 45298-90-6

CMF C8 F17 O3 S

$^{-}O_3S-(CF_2)_7-CF_3$

L15 ANSWER 36 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN

ACCESSION NUMBER: 2001:421234 HCAPLUS

DOCUMENT NUMBER: 135:53496

TITLE: Positive photoresist compositions  
for manufacture of semiconductor devices

INVENTOR(S): Sato, Kenichiro; Kodama, Kunihiro; Mizutani, Kazuyoshi

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 59 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001159822	A2	20010612	JP 1999-343713	19991202

PRIORITY APPLN. INFO.: JP 1999-343713 19991202

OTHER SOURCE(S): MARPAT 135:53496

IT 258341-99-0

RL: TEM (Technical or engineered material use); USES (Uses)  
(photoacid generators; improvement of exposure  
margin in pos. photoresists for manufacture of  
semiconductor devices)

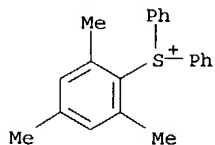
RN 258341-99-0 HCAPLUS

CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6

CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

$-\text{O}_3\text{S}^-(\text{CF}_2)_7-\text{CF}_3$

L15 ANSWER 37 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2001:388948 HCAPLUS  
DOCUMENT NUMBER: 135:12122  
TITLE: **Positive-working photoresist**  
composition containing sulfonium compound acid  
generator  
INVENTOR(S): Sato, Kenichiro; Mizutani, Kazuyoshi  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 65 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 4  
PATENT INFORMATION:

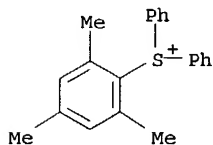
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001147536	A2	20010529	JP 1999-331785	19991122
US 6506535	B1	20030114	US 2000-698221	20001030

PRIORITY APPLN. INFO.: JP 1999-307317 A 19991028  
JP 1999-331785 A 19991122  
JP 1999-338487 A 19991129  
JP 1999-343714 A 19991202

OTHER SOURCE(S): MARPAT 135:12122  
IT 258341-99-0  
RL: TEM (Technical or engineered material use); USES (Uses)  
(acid generator; photoresist composition  
containing sulfonium compound acid generator,  
acid-decomposable polymer, basic compound and surfactant)  
RN 258341-99-0 HCAPLUS  
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

$-\text{O}_3\text{S}^-(\text{CF}_2)_7-\text{CF}_3$

L15 ANSWER 38 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2001:319605 HCAPLUS  
DOCUMENT NUMBER: 134:334291  
TITLE: **Positive-working photoresist**  
composition  
INVENTOR(S): Sato, Kenichiro; Mizutani, Kazuyoshi; Yasunami,

Shoichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Eur. Pat. Appl., 80 pp.  
CODEN: EPXXDW  
DOCUMENT TYPE: Patent  
LANGUAGE: English  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

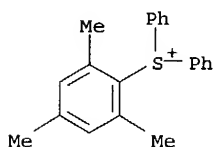
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1096319	A1	20010502	EP 2000-123359	20001030
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO				
JP 2001194794	A2	20010719	JP 2000-328968	20001027
JP 2001201857	A2	20010727	JP 2000-329053	20001027
US 6589705	B1	20030708	US 2000-698190	20001030
PRIORITY APPLN. INFO.:			JP 1999-309587	A 19991029
			JP 1999-319837	A 19991110

IT 258341-99-0P  
RL: IMF (Industrial manufacture); PEP (Physical, engineering or chemical process); SPN (Synthetic preparation); PREP (Preparation); PROC (Process) (synthesis of photoacid generator for pos.-working photoresist composition used in manufacture of semiconductor integrated circuit element)

RN 258341-99-0 HCAPLUS  
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

$-\text{O}_3\text{S}^-(\text{CF}_2)_7-\text{CF}_3$

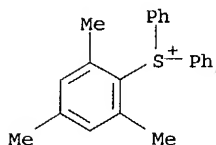
REFERENCE COUNT: 5 THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L15 ANSWER 39 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2001:133886 HCAPLUS  
DOCUMENT NUMBER: 134:200519  
TITLE: Method for positive-working resist pattern formation using ArF excimer laser  
INVENTOR(S): Nakao, Hajime; Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 89 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001051421	A2	20010223	JP 1999-228617	19990812
PRIORITY APPLN. INFO.:			JP 1999-228617	19990812
IT 258341-99-0P				
RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (photoacid generator for pos.-working resist pattern formation)				
RN 258341-99-0 HCAPLUS				
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid (1:1) (9CI) (CA INDEX NAME)				

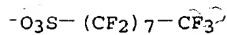
CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S



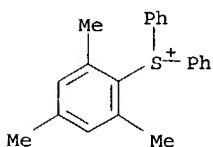
L15 ANSWER 40 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2000:669837 HCAPLUS  
Correction of: 2000:532748  
DOCUMENT NUMBER: 133:215466  
Correction of: 133:157673  
TITLE: Far UV-sensitive **positive**-working  
**photoresist** compositions  
INVENTOR(S): Sato, Kenichiro; Kodama, Kunihiro; Aogo, Toshiaki  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 34 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2000214588	A2	20000804	JP 1999-18511	19990127
US 2002098440	A1	20020725	US 2000-492848	20000127
US 6544715	B2	20030408		

PRIORITY APPLN. INFO.: JP 1999-18511 A 19990127  
IT 258341-99-0P  
RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
(photosensitive **acid generator** for far-UV-sensitive **photoresist** compns.)  
RN 258341-99-0 HCAPLUS  
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid (1:1) (9CI) (CA INDEX NAME)

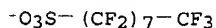
CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S



L15 ANSWER 41 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN

ACCESSION NUMBER: 2000:585594 HCAPLUS  
DOCUMENT NUMBER: 133:200844  
TITLE: Positive-working photoresist  
composition containing polymer having sulfonate group  
INVENTOR(S): Sato, Kenichiro; Kodama, Kunihiro; Aogo, Toshiaki  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 47 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 2  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2000231194	A2	20000822	JP 1999-240600	19990826
US 6576392	B1	20030610	US 1999-456827	19991206

PRIORITY APPLN. INFO.: JP 1998-347193 A 19981207  
JP 1999-30209 A 19990208  
JP 1999-240600 A 19990826

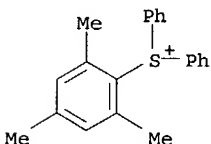
IT 258341-99-0  
RL: TEM (Technical or engineered material use); USES (Uses)  
(photoresist composition containing alkali-soluble polymer with sulfonate group)

RN 258341-99-0 HCAPLUS

CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8-heptadecafluoro-1-octanesulfonic acid  
(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

$-\text{O}_3\text{S}^-(\text{CF}_2)_7-\text{CF}_3$

L15 ANSWER 42 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2000:563063 HCAPLUS  
DOCUMENT NUMBER: 133:185531  
TITLE: Positive-working photoresist  
composition for far UV exposure  
INVENTOR(S): Sato, Kenichiro; Ohashi, Hidekazu; Aogo, Toshiaki  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 31 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 2  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2000227659	A2	20000815	JP 1999-30209	19990208
US 6576392	B1	20030610	US 1999-456827	19991206

PRIORITY APPLN. INFO.: JP 1998-347193 A 19961207  
JP 1999-30209 A 19990208  
JP 1999-240600 A 19990826

IT 258341-99-0P  
RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
(photoacid generator; photoresist composition containing photoacid generator, alkali-soluble resin, and sulfonic acid generator)

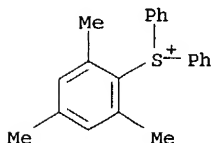
RN 258341-99-0 HCAPLUS

CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8-heptadecafluoro-1-octanesulfonic acid

(1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

L15 ANSWER 43 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2000:474297 HCAPLUS  
DOCUMENT NUMBER: 133:96798  
TITLE: Pattern formation using **positive-working photoresist**  
INVENTOR(S): Sato, Kenichiro; Nakao, Hajime; Kawabe, Yasumasa  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 32 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2000194135	A2	20000714	JP 1998-371210	19981225

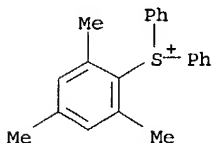
PRIORITY APPLN. INFO.: JP 1998-371210 19981225

IT 258341-99-0P  
RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
(photoresist composition containing acid generator and polymer with alicyclic protective group)

RN 258341-99-0 HCAPLUS  
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptafluoro-1-octanesulfonic acid (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

L15 ANSWER 44 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2000:454439 HCAPLUS  
DOCUMENT NUMBER: 133:96789  
TITLE: **Positive-working photoresist**



composition for far UV ray exposure  
 INVENTOR(S): Sato, Kenichiro  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 30 pp.  
 CODEN: JKXXAF  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2000187327	A2	20000704	JP 1998-327056	19981117

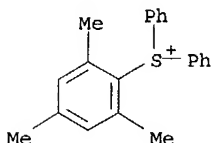
PRIORITY APPLN. INFO.: JP 1998-293986 A 19981015

IT 258341-99-0P  
 RL: MOA (Modifier or additive use); PNU (Preparation, unclassified); PREP (Preparation); USES (Uses)  
 (photoacid generator; pos.-working  
 photoresist composition for far UV ray exposure)

RN 258341-99-0 HCAPLUS  
 CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptadecafluoro-1-octanesulfonic acid  
 (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
 CMF C21 H21 S



CM 2

CRN 45298-90-6  
 CMF C8 F17 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

L15 ANSWER 45 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
 ACCESSION NUMBER: 2000:440245 HCAPLUS  
 DOCUMENT NUMBER: 133:81565  
 TITLE: Positive-working photoresist  
 composition for far UV ray exposure  
 INVENTOR(S): Sato, Kenichiro; Kodama, Kunihiro  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 25 pp.  
 CODEN: JKXXAF

DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2000181054	A2	20000630	JP 1998-327055	19981117
JP 3476374	B2	20031210		

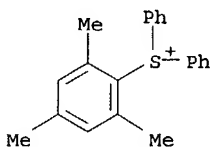
PRIORITY APPLN. INFO.: JP 1998-288108 A 19981009  
 OTHER SOURCE(S): MARPAT 133:81565

IT 258341-99-0P  
 RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
 (photo acid generator; pos.-working  
 photoresist composition for far UV ray exposure)

RN 258341-99-0 HCAPLUS  
 CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with  
 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptadecafluoro-1-octanesulfonic acid  
 (1:1) (9CI) (CA INDEX NAME)

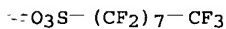
CM 1

CRN 47191-44-6  
 CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S



L15 ANSWER 46 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
 ACCESSION NUMBER: 2000:357221 HCAPLUS  
 DOCUMENT NUMBER: 133:11016  
 TITLE: Positive-working photoresist  
 composition for far ultraviolet ray exposure  
 INVENTOR(S): Sato, Kenichiro; Kodama, Kunihiro; Aogo, Toshiaki  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 35 pp.  
 CODEN: JKXXAF  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 2  
 PATENT INFORMATION:

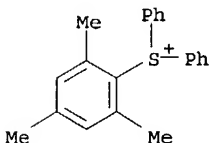
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2000147776	A2	20000526	JP 1998-327054	19981117
US 2002081518	A1	20020627	US 1999-438789	19991112
US 6420082	B1	20020716		

PRIORITY APPLN. INFO.: JP 1998-323783 A 19981113  
 JP 1998-327054 A 19981117

IT 258341-99-0P  
 RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
 (pos. photoresist containing acid generator and alkali-soluble resin)  
 RN 258341-99-0 HCAPLUS  
 CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptadecafluoro-1-octanesulfonic acid (1:1) (9CI) (CA INDEX NAME)

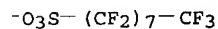
CM 1

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CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S



L15 ANSWER 47 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
 ACCESSION NUMBER: 2000:357220 HCAPLUS  
 DOCUMENT NUMBER: 133:11015  
 TITLE: Positive-working photoresist  
 composition for far ultraviolet ray exposure  
 INVENTOR(S): Sato, Kenichiro; Kodama, Kunihiro; Aogo, Toshiaki  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 31 pp.

CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

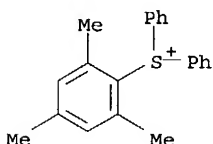
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2000147775	A2	20000526	JP 1998-327052	19981117
PRIORITY APPLN. INFO.:			JP 1998-327052	19981117

IT 258341-99-0P  
RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
(photoresist composition containing photoacid generator and alkali-soluble resin)

RN 258341-99-0 HCAPLUS  
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptadecafluoro-1-octanesulfonic acid (1:1) (9CI) (CA INDEX NAME)

CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S

-O<sub>3</sub>S- (CF<sub>2</sub>)<sub>7</sub>-CF<sub>3</sub>

L15 ANSWER 48 OF 48 HCAPLUS COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 2000:115245 HCAPLUS  
DOCUMENT NUMBER: 132:173394  
TITLE: Positive-working photoresist composition for far ultraviolet ray exposure  
INVENTOR(S): Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 41 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

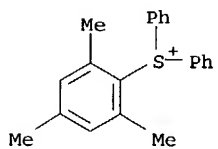
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2000047387	A2	20000218	JP 1998-212878	19980728
PRIORITY APPLN. INFO.:			JP 1998-212878	19980728

IT 258341-99-0P  
RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
(pos. photoresist composition containing sulfonic acid generating compound and alkali-soluble alicyclic polymer)

RN 258341-99-0 HCAPLUS  
CN Sulfonium, diphenyl(2,4,6-trimethylphenyl)-, salt with 1,1,2,2,3,3,4,4,5,5,6,6,7,7,8,8,8-heptadecafluoro-1-octanesulfonic acid (1:1) (9CI) (CA INDEX NAME)

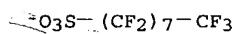
CM 1

CRN 47191-44-6  
CMF C21 H21 S



CM 2

CRN 45298-90-6  
CMF C8 F17 O3 S



L Number	Hits	Search Text	DB	Time stamp
1	2	ep-1199603-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 17:09
-	2	("20030027061").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 10:03
-	0	20030027061.URPN.	USPAT	2003/08/06 16:35
-	0	alpha,alpha-difluoroalkyl adj sulfonic adj acid	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/06 16:36
-	2	\$.difluoroalkyl adj sulfonic adj acid	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/06 16:37
-	2	\$.difluoro\$8yl adj sulfonic adj acid	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/06 16:40
-	15153	(\$5ACID NEAR GENERAT\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 10:28
-	21	DIFLUORO\$ NEAR SULFONIC	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/06 16:41
-	35	FLUOR\$8 NEAR (ALKANESULFONIC ADJ ACID)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 12:42
-	4	(FLUOR\$8 NEAR (ALKANESULFONIC ADJ ACID)) AND (BINDER RESIN RESIST PHOTORESIST)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/06 17:29
-	3	6358665.URPN.	USPAT	2003/08/06 17:21
-	60	CAMERON-JAMES CAMERON-JAMES-F CAMERON-JAMES-FIELD (zydowsky-thomas.in.) (zydowsky-t.in.) (zydowsky-thomas-m.in.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 10:27
-	38	(CAMERON-JAMES CAMERON-JAMES-F CAMERON-JAMES-FIELD (zydowsky-thomas.in.) (zydowsky-t.in.) (zydowsky-thomas-m.in.)) and (resist photoresist resin binder)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 10:28
-	15196	(\$5ACID NEAR GENERAT\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 10:28
-	26	((CAMERON-JAMES CAMERON-JAMES-F CAMERON-JAMES-FIELD (zydowsky-thomas.in.) (zydowsky-t.in.) (zydowsky-thomas-m.in.)) and (resist photoresist resin binder)) and ((\$5ACID NEAR GENERAT\$4) )	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 10:28
-	27	(CAMERON-JAMES CAMERON-JAMES-F CAMERON-JAMES-FIELD (zydowsky-thomas.in.) (zydowsky-t.in.) (zydowsky-thomas-m.in.)) and ((\$5ACID NEAR GENERAT\$4) )	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 12:41
-	7	(photoacid near generator) same (phosphoric adj acid)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 12:35
-	4518	method same prepar\$4 same (sulfonic adj acid)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 12:54
-	1907	onium adj compounds	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 15:17

-	996	(resist photoresist) and (\$5acid near generator) and (sulfonic adj acid)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 15:18
-	877	((resist photoresist) and (\$5acid near generator) and (sulfonic adj acid)) and (onium sulfonium iodonium sulfonate nonionic non-ionic)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 15:19
-	0	((resist photoresist) and (\$5acid near generator) and (sulfonic adj acid)) and (onium sulfonium iodonium sulfonate nonionic non-ionic)) and (430/270.1.ccls)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 15:19
-	559	((resist photoresist) and (\$5acid near generator) and (sulfonic adj acid)) and (onium sulfonium iodonium sulfonate nonionic non-ionic)) and (430/270.1.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 15:19
-	374	((resist photoresist) and (\$5acid near generator) and (sulfonic adj acid)) and (onium sulfonium iodonium sulfonate nonionic non-ionic)) and (430/270.1.ccls.)	USPAT	2003/08/07 15:56
-	0	wo-9410608-\$.did.	USPAT	2003/08/07 17:27
-	59	n-sulfonyloxyimide	USPAT	2004/04/07 15:23
-	28	n-sulfonyloxyimide and (((resist photoresist) and (\$5acid near generator) and (sulfonic adj acid)) and (onium sulfonium iodonium sulfonate nonionic non-ionic)) and (430/270.1.ccls.))	USPAT	2003/08/07 15:57
-	0	wo-940010608-\$.did.	USPAT	2003/08/07 17:27
-	0	wo-94010608-\$.did.	USPAT	2003/08/07 17:28
-	4	((("5296332") or ("6280911"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/07 18:11
-	1000901	positive	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/07 15:18
-	440581	photoresist resist	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/07 15:18
-	5686	(photoacid acid) adj labile	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/07 15:18
-	4875	(photoacid acid) adj generator	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/07 15:19
-	153470	sulfonic adj acid	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/07 15:19
-	432	positive AND (photoresist resist) AND ((photoacid acid) adj labile) AND ((photoacid acid) adj generator) AND (sulfonic adj acid)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/07 15:19
-	67	n-sulfonyloxyimide	USPAT	2004/04/07 15:24
-	32	(positive AND (photoresist resist) AND ((photoacid acid) adj labile) AND ((photoacid acid) adj generator) AND (sulfonic adj acid)) and n-sulfonyloxyimide	USPAT	2004/04/07 15:24
-	107	n-sulfonyloxyimide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 12:42
-	2	difluoroalkylsulfonic (difluoroalkyl adj sulfonic)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/07 15:33

-	6	difluoro\$5ylsulfonic (difluoro\$5yl adj sulfonic)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/07 15:33
-	1	((positive AND (photoresist resist) AND ((photoacid acid) adj labile) AND ((photoacid acid) adj generator) AND (sulfonic adj acid)) and ((difluoroalkylsulfonic (difluoroalkyl adj sulfonic) ) (difluoro\$5ylsulfonic (difluoro\$5yl adj sulfonic) ) )	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/07 15:33
-	6	(difluoroalkylsulfonic (difluoroalkyl adj sulfonic) ) (difluoro\$5ylsulfonic (difluoro\$5yl adj sulfonic) )	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/07 15:36
-	52	((positive AND (photoresist resist) AND ((photoacid acid) adj labile) AND ((photoacid acid) adj generator) AND (sulfonic adj acid)) and n-sulfonyloxyimide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 12:20
-	2	("6136501").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 10:03
-	4	wo-9410608-\$.did. ep-708368-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 12:21
-	107	n-sulfonyloxyimide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 12:42
-	32	(CAMERON-JAMES CAMERON-JAMES-F CAMERON-JAMES-FIELD (zydowsky-thomas.in.) (zydowsky-t.in.) (zydowsky-thomas-m.in.) and ((\$ACID NEAR GENERAT\$4) )	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 12:42
-	37	FLUOR\$8 NEAR (ALKANESULFONIC ADJ ACID)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 12:46
-	2	("5442023"   "5773191").PN.	USPAT	2004/04/08 12:50
-	5	6358665.URPN.	USPAT	2004/04/08 12:52
-	5	6358665.URPN.	USPAT	2004/04/08 12:59
-	2	ep-1199603-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 15:07
-	0	1199603.URPN.	USPAT	2004/04/08 15:06
-	5	ep-1033624-\$.did. ep-693468-\$.did. dd-295421-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 15:08
-	7	ep-1033624-\$.did. ep-693468-\$.did. dd-295421-\$.did. ep-1041442-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/08 17:09